

Erratum to: A Novel Exponential Approximation with ± 0.21 dB Error for Realizing an Improved CMOS Exponential Function Generator

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The authors regret the following errors occurred in the original publication of the article. The corrected text has been presented with this erratum.

In Abstract section, the last sentence should read “The post-layout simulation results of the proposed CMOS exponential generator, thus, consume only ≈ 119 nW power and produce 51.6 dB range of linear-in-dB output with only ± 0.21 dB error while occupying an area of 0.0026 mm^2 ”.

In Table 2, last row, the first column “Parameter” should be, “Area (mm^2)” and the corrected value for this work should be “0.0026 instead of 0.26.”

In the section titled “Simulation Results,” last para, the sentence should read, “The silicon area required for the proposed CMOS exponential generator based on the new MPTEA is found out to be 0.0026 mm^2 .”

In Conclusion section, the sentence should read, “The silicon area requirement for the proposed CMOS exponential generator based on the new MPTEA is found out to be 0.0026 mm^2 .”

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